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a semiconductor substrate having a substrate surface, a first
conductive region and a second conductive region;

↓ B1
cont. a gate oxide disposed on said substrate surface;

a gate disposed on said gate oxide over an area between said
first conductive region and said second conductive region and
having at least one side wall adjacent at least one of said
conductive regions;

a silicon oxide passivation layer disposed on said side wall
of said gate; and

an insulating silicon nitride spacer disposed on said silicon
oxide passivation layer, said spacer acting as an oxidation
barrier;

said gate oxide insulating said gate from said semiconductor
substrate and having a thickened area in a region below said
side wall of said gate.
